

## Description

The HSU3002 is the high cell density trenched N-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

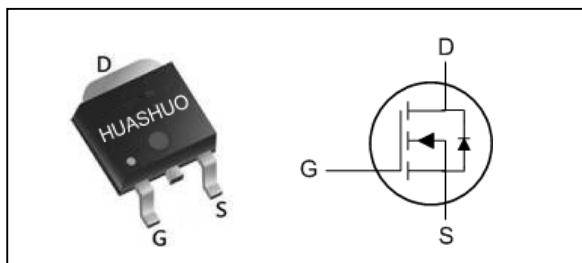
The HSU3002 meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

- 100% EAS Guaranteed
- Green Device Available
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- Advanced high cell density Trench technology

## Product Summary

V <sub>DS</sub>	30	V
R <sub>DS(ON),max</sub>	18	mΩ
I <sub>D</sub>	30	A

## TO252 Pin Configuration



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V <sub>DS</sub>	Drain-Source Voltage	30	V
V <sub>GS</sub>	Gate-Source Voltage	±20	V
I <sub>D</sub> @T <sub>C</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	30	A
I <sub>D</sub> @T <sub>C</sub> =100°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	18	A
I <sub>D</sub> @T <sub>A</sub> =25°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	8.2	A
I <sub>D</sub> @T <sub>A</sub> =70°C	Continuous Drain Current, V <sub>GS</sub> @ 10V <sup>1</sup>	6.5	A
I <sub>DM</sub>	Pulsed Drain Current <sup>2</sup>	60	A
EAS	Single Pulse Avalanche Energy <sup>3</sup>	22.1	mJ
I <sub>AS</sub>	Avalanche Current	21	A
P <sub>D</sub> @T <sub>C</sub> =25°C	Total Power Dissipation <sup>4</sup>	25	W
P <sub>D</sub> @T <sub>A</sub> =25°C	Total Power Dissipation <sup>4</sup>	2	W
T <sub>STG</sub>	Storage Temperature Range	-55 to 150	°C
T <sub>J</sub>	Operating Junction Temperature Range	-55 to 150	°C

## Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
R <sub>θJA</sub>	Thermal Resistance Junction-ambient (Steady State) <sup>1</sup>	---	62	°C/W
R <sub>θJC</sub>	Thermal Resistance Junction-Case <sup>1</sup>	---	5	°C/W



**Electrical Characteristics ( $T_J=25^\circ\text{C}$ , unless otherwise noted)**

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}$ , $I_D=250\mu\text{A}$	30	---	---	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_J$	BVDSS Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_D=1\text{mA}$	---	0.023	---	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{\text{GS}}=10\text{V}$ , $I_D=15\text{A}$	---	15	18	$\text{m}\Omega$
		$V_{\text{GS}}=4.5\text{V}$ , $I_D=10\text{A}$	---	22	30	
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{GS}}=V_{\text{DS}}$ , $I_D=250\mu\text{A}$	1.2	1.5	2.5	V
$\Delta V_{\text{GS}(\text{th})}$	$V_{\text{GS}(\text{th})}$ Temperature Coefficient		---	-5.2	---	$\text{mV}/^\circ\text{C}$
$I_{\text{DSS}}$	Drain-Source Leakage Current	$V_{\text{DS}}=24\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=25^\circ\text{C}$	---	---	1	$\text{uA}$
		$V_{\text{DS}}=24\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $T_J=55^\circ\text{C}$	---	---	5	
$I_{\text{GSS}}$	Gate-Source Leakage Current	$V_{\text{GS}}=\pm 20\text{V}$ , $V_{\text{DS}}=0\text{V}$	---	---	$\pm 100$	nA
$g_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}=5\text{V}$ , $I_D=15\text{A}$	---	21.6	---	S
$R_g$	Gate Resistance	$V_{\text{DS}}=0\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	2.5	5	$\Omega$
$Q_g$	Total Gate Charge (4.5V)	$V_{\text{DS}}=15\text{V}$ , $V_{\text{GS}}=4.5\text{V}$ , $I_D=15\text{A}$	---	6.2	8.7	$\text{nC}$
$Q_{\text{gs}}$	Gate-Source Charge		---	2.4	3.4	
$Q_{\text{gd}}$	Gate-Drain Charge		---	2.5	3.5	
$T_{\text{d}(\text{on})}$	Turn-On Delay Time	$V_{\text{DD}}=15\text{V}$ , $V_{\text{GS}}=10\text{V}$ , $R_G=3.3\Omega$ , $I_D=15\text{A}$	---	3	6.0	$\text{ns}$
$T_r$	Rise Time		---	7.6	14	
$T_{\text{d}(\text{off})}$	Turn-Off Delay Time		---	21	42	
$T_f$	Fall Time		---	4	8	
$C_{\text{iss}}$	Input Capacitance	$V_{\text{DS}}=15\text{V}$ , $V_{\text{GS}}=0\text{V}$ , $f=1\text{MHz}$	---	572	801	$\text{pF}$
$C_{\text{oss}}$	Output Capacitance		---	81	113	
$C_{\text{rss}}$	Reverse Transfer Capacitance		---	65	91	

**Diode Characteristics**

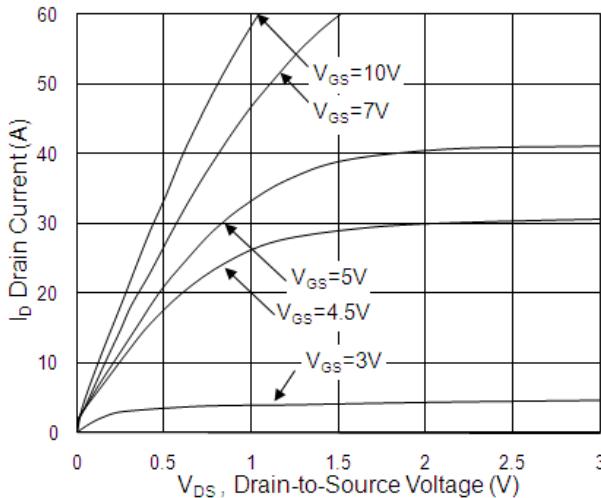
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
$I_S$	Continuous Source Current <sup>1,5</sup>	$V_G=V_D=0\text{V}$ , Force Current	---	---	30	A
$I_{\text{SM}}$	Pulsed Source Current <sup>2,5</sup>		---	---	60	A
$V_{\text{SD}}$	Diode Forward Voltage <sup>2</sup>	$V_{\text{GS}}=0\text{V}$ , $I_S=1\text{A}$ , $T_J=25^\circ\text{C}$	---	---	1.2	V
$t_{\text{rr}}$	Reverse Recovery Time	$I_F=15\text{A}$ , $dI/dt=100\text{A}/\mu\text{s}$ ,	---	17	---	$\text{nS}$
$Q_{\text{rr}}$	Reverse Recovery Charge	$T_J=25^\circ\text{C}$	---	3	---	$\text{nC}$

Note :

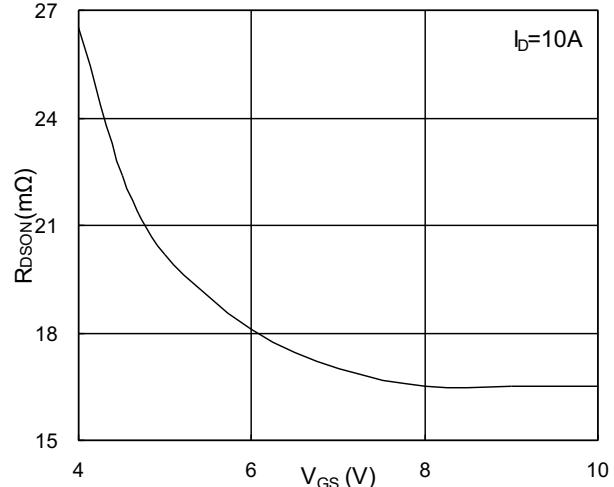
- 1.The data tested by surface mounted on a 1 inch<sup>2</sup> FR-4 board with 2OZ copper.
- 2.The data tested by pulsed , pulse width  $\leq 300\mu\text{s}$  , duty cycle  $\leq 2\%$
- 3.The EAS data shows Max. rating . The test condition is  $V_{\text{DD}}=25\text{V}$ ,  $V_{\text{GS}}=10\text{V}$ ,  $L=0.1\text{mH}$ ,  $I_{\text{AS}}=21\text{A}$
- 4.The power dissipation is limited by  $150^\circ\text{C}$  junction temperature
- 5.The data is theoretically the same as  $I_D$  and  $I_{\text{DM}}$  , in real applications , should be limited by total power dissipation.



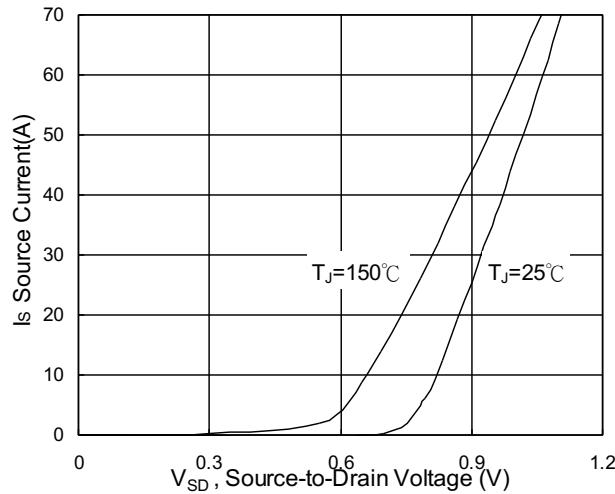
### Typical Characteristics



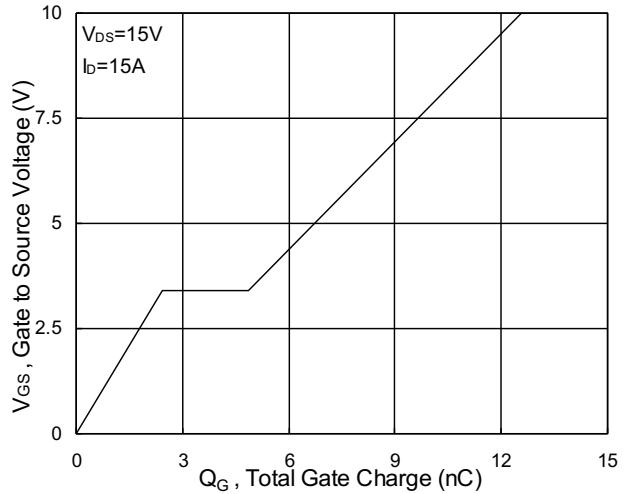
**Fig.1 Typical Output Characteristics**



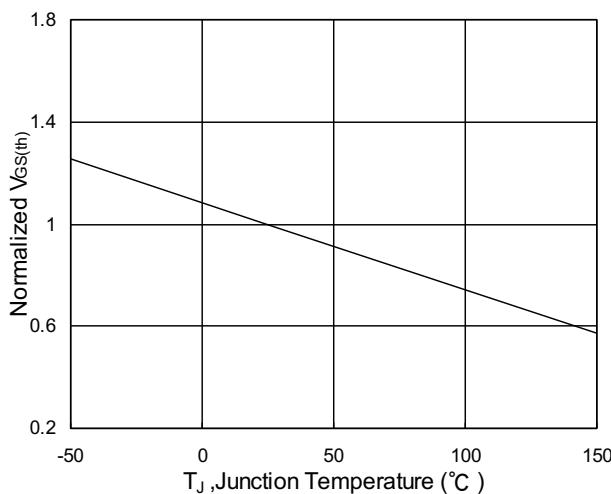
**Fig.2 On-Resistance v.s Gate-Source**



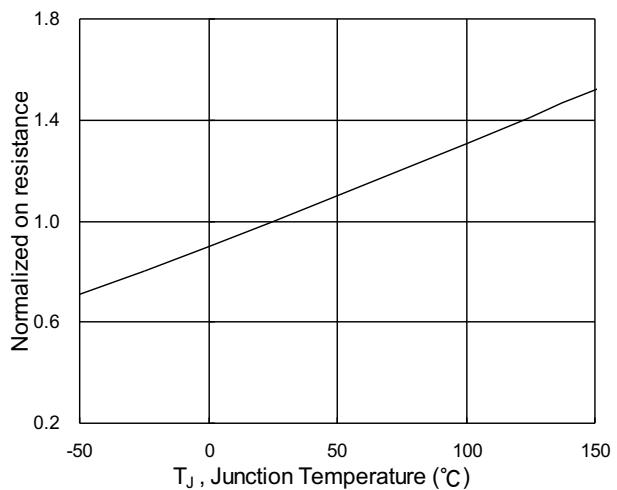
**Fig.3 Forward Characteristics Of Reverse**



**Fig.4 Gate-Charge Characteristics**



**Fig.5 Normalized  $V_{GS(th)}$  v.s  $T_J$**



**Fig.6 Normalized  $R_{DS(on)}$  v.s  $T_J$**



HUASHUO  
SEMICONDUCTOR

HSU3002

N-Ch 30V Fast Switching MOSFETs

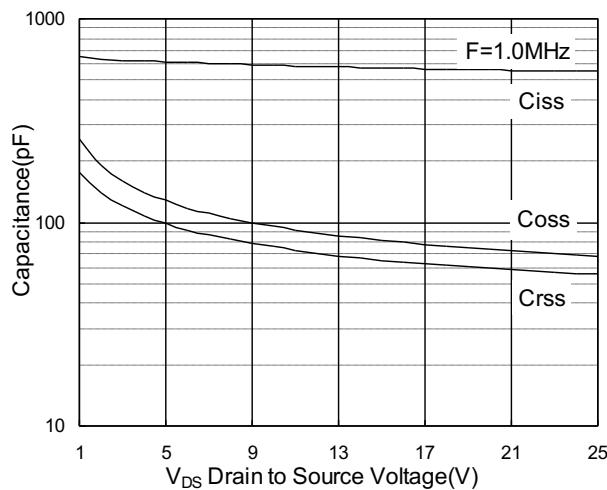


Fig.7 Capacitance

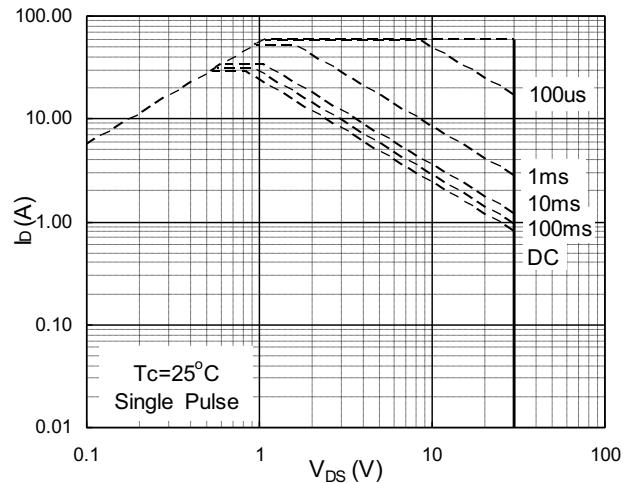


Fig.8 Safe Operating Area

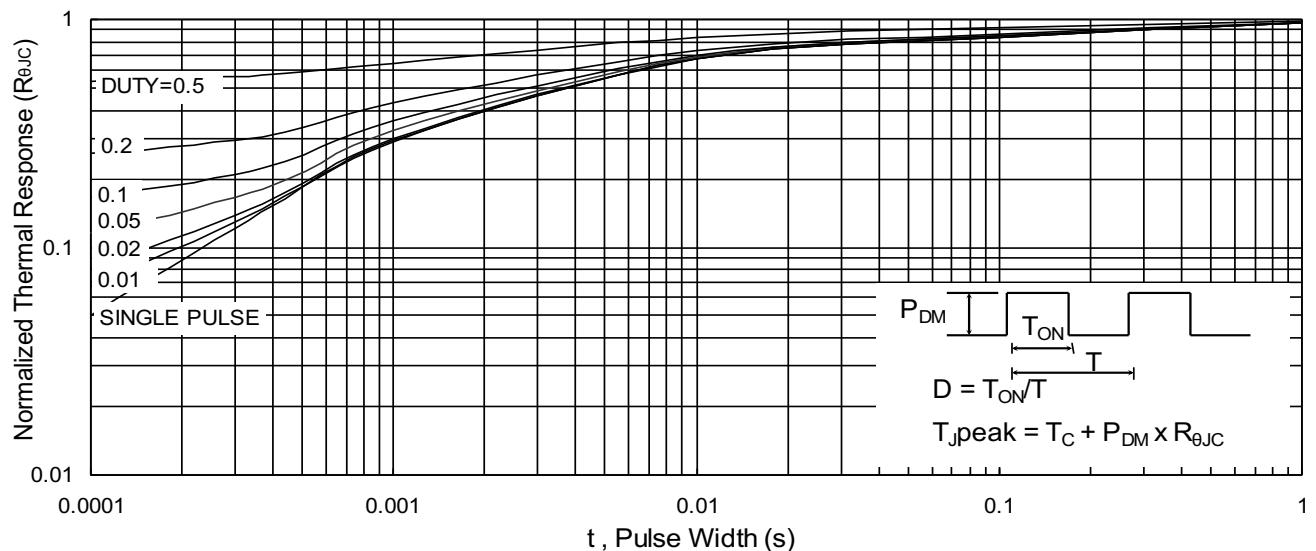


Fig.9 Normalized Maximum Transient Thermal Impedance

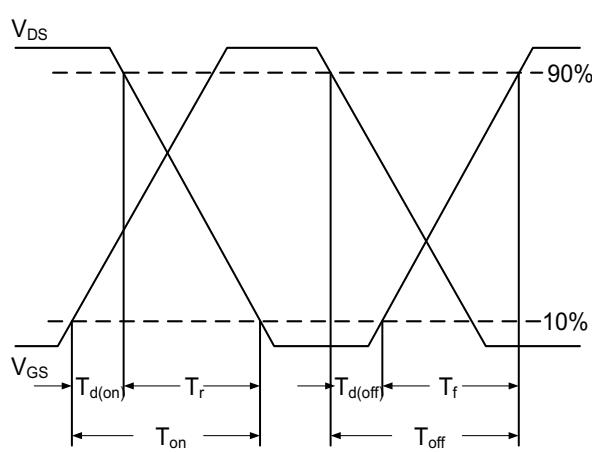


Fig.10 Switching Time Waveform

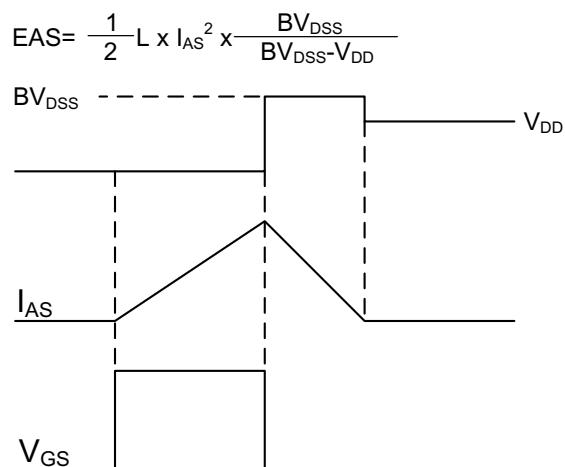
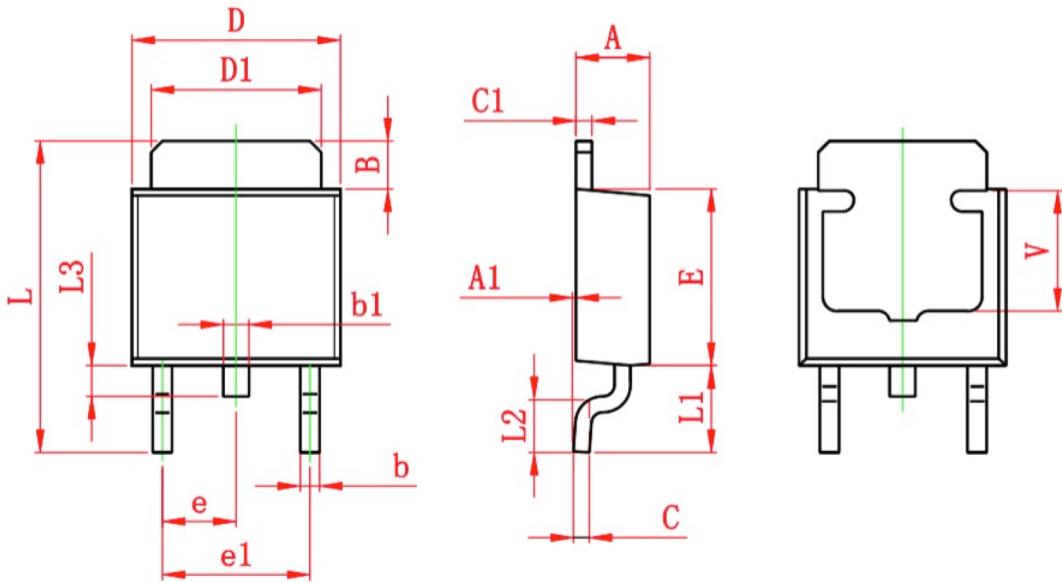


Fig.11 Unclamped Inductive Switching



## Ordering Information

Part Number	Package code	Packaging
HSU3002	TO252-2	2500/Tape&Reel



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	2.200	2.400	0.087	0.094
A1	0.000	0.127	0.000	0.005
B	1.350	1.650	0.053	0.065
b	0.500	0.700	0.020	0.028
b1	0.700	0.900	0.028	0.035
c	0.430	0.580	0.017	0.023
c1	0.430	0.580	0.017	0.023
D	6.350	6.650	0.250	0.262
D1	5.200	5.400	0.205	0.213
E	5.400	5.700	0.213	0.224
e	2.300 TYP.		0.091 TYP.	
e1	4.500	4.700	0.177	0.185
L	9.500	9.900	0.374	0.390
L1	2.550	2.900	0.100	0.114
L2	1.400	1.780	0.055	0.070
L3	0.600	0.900	0.024	0.035
V	3.800 REF.		0.150 REF.	